

## R-C Thermal Model Parameters

### DESCRIPTION

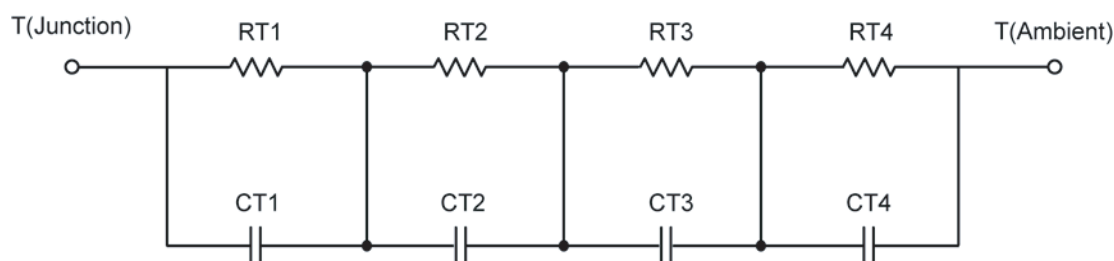
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

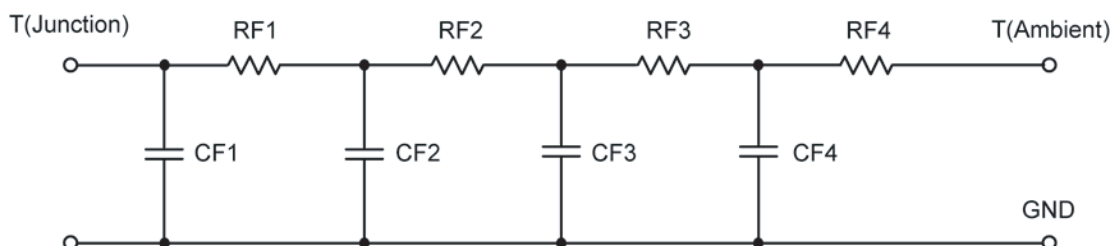
*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	13.2599	N/A	12.1099
RT2	4.7039	N/A	1.8151
RT3	21.6204	N/A	4.3990
RT4	40.4158	N/A	5.6760
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	43.6643 m	N/A	142.6877 m
CT2	4.8035 m	N/A	481.3369 u
CT3	411.6817 m	N/A	9.4824 m
CT4	3.3774	N/A	37.2536 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION**

**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	5.9882	N/A	2.4465
RF2	16.7624	N/A	7.3578
RF3	25.8275	N/A	8.3729
RF4	31.4219	N/A	5.8228
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	4.8233 m	N/A	483.9257 u
CF2	37.3844 m	N/A	8.0507 m
CF3	496.3225 m	N/A	48.4346 m
CF4	4.1250	N/A	266.9178 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

